Green Package

PFI6N80G / PFB6N80G

800V N-Channel MOSFET

FEATURES

- Originative New Design
- 100% EAS Test
- Rugged Gate Oxide Technology
- Extremely Low Intrinsic Capacitances
- Remarkable Switching Characteristics
- Unequalled Gate Charge : 22.2 nC (Typ.)
- Extended Safe Operating Area
- Lower $R_{DS(ON)}$: 2.4 Ω (Typ.) @V_{GS}=10V

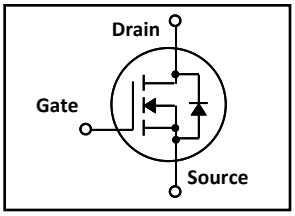
APPLICATION

- Low power battery chargers
- Switch mode power supply (SMPS)
- AC adaptors

BV_{DSS} = 800 V

$R_{DS(on)}$ = 2.4 Ω

I_D = 5.5 A



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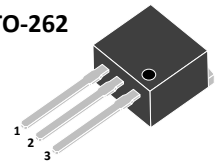

1.Gate 2. Drain 3. Source

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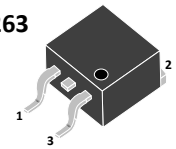


1.Gate 2. Drain 3. Source

Absolute Maximum Ratings

T_C=25℃ unless otherwise specified

Symbol	Parameter	Value	Units
V_{DSS}	Drain-Source Voltage	800	V
I_D	Drain Current – Continuous (T_C = 25°C)	5.5	A
	Drain Current – Continuous (T_C = 100°C)	3.5	A
I_{DM}	Drain Current – Pulsed (Note 1)	22	A
V_{GS}	Gate-Source Voltage	±30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	600	mJ
I_{AR}	Avalanche Current (Note 1)	5.5	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	17.9	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
P_D	Total Power Dissipation (TA=25°C) *	2.0	W
	Power Dissipation (T_C = 25°C)	179	W
	- Derate above 25°C	1.43	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	°C
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C

* Drain current limited by maximum junction temperature.

Thermal Resistance Characteristics

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Junction-to-Case	0.7	°C/W
$R_{\theta JA}$	Junction-to-Ambient(*1 in^2 Pad of 2-oz Copper), Max.	40	
$R_{\theta JA}$	Junction-to-Ambient(Min. Pad of 2-oz Copper), Max.	62.5	

Electrical Characteristics T_C=25°C unless otherwise specified

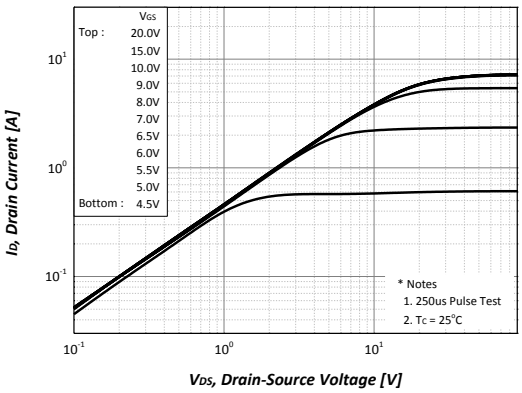
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
On Characteristics						
V_{GS}	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 uA	2.5	--	4.5	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 3.0 A	--	2.4	3.0	Ω
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 uA	800	--	--	V
ΔBV_{DSS} /ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 uA, Referenced to25°C	--	0.88	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 800 V, V_{GS} = 0 V	--	--	10	uA
		V_{DS} = 640 V, T_C = 125℃	--	--	100	uA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30 V, V_{DS} = 0 V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30 V, V_{DS} = 0 V	--	--	-100	nA
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	--	1175	1530	pF
C_{oss}	Output Capacitance		--	76	100	pF
C_{rss}	Reverse Transfer Capacitance		--	22	30	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Time	V_{DS} = 400 V, I_D = 6.0 A, R_G = 25 Ω, R_L = 67 Ω (Note 4,5)	--	26	55	ns
t_r	Turn-On Rise Time		--	18	40	ns
$t_{d(off)}$	Turn-Off Delay Time		--	53	110	ns
t_f	Turn-Off Fall Time		--	28	60	ns
Q_g	Total Gate Charge	V_{DS} = 640 V, I_D = 6.0 A, V_{GS} = 10 V (Note 4,5)	--	22.2	33	nC
Q_{gs}	Gate-Source Charge		--	8.5	--	nC
Q_{gd}	Gate-Drain Charge		--	4.2	--	nC
Source-Drain Diode Maximum Ratings and Characteristics						
I_S	Continuous Source-Drain Diode Forward Current		--	--	5.5	A
I_{SM}	Pulsed Source-Drain Diode Forward Current		--	--	22	
V_{SD}	Source-Drain Diode Forward Voltage	I_S = 6.0 A, V_{GS} = 0 V	--	--	1.5	V
trr	Reverse Recovery Time	I_S = 6.0 A, V_{GS} = 0 V di_F/dt = 100 A/us (Note 4)	--	530	--	ns
Qrr	Reverse Recovery Charge		--	4.3	--	uC

Notes ;

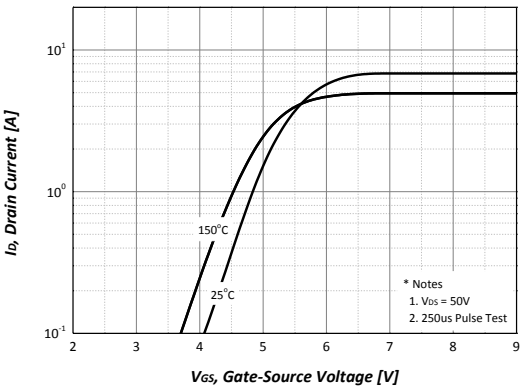
1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. I_{AS}=6.0A, V_{DD}=50V, R_G=25Ω, Starting T_J=25°C
3. I_{SD}≤6.0A, di/dt≤300A/μs, V_{DD}≤BV_{DSS} , Starting T_J=25°C
4. Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%
5. Essentially Independent of Operating Temperature

Typical Characteristics

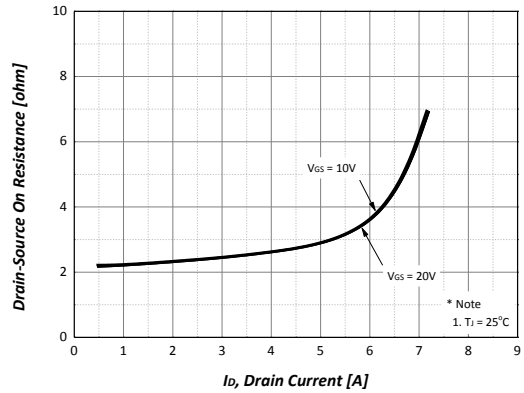
On Region Characteristics



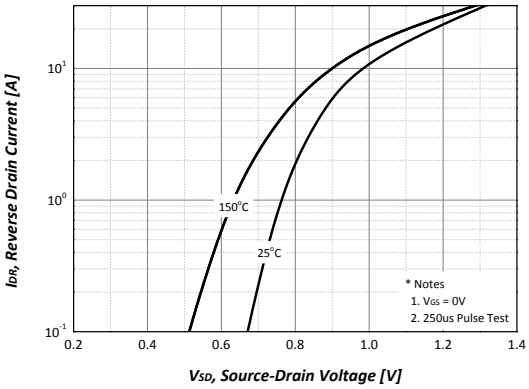
Transfer Characteristics



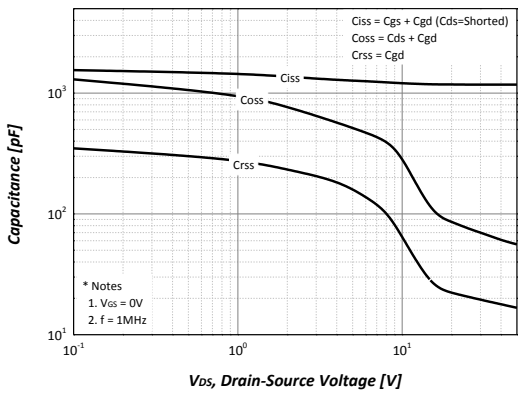
Static Drain-Source On Resistance



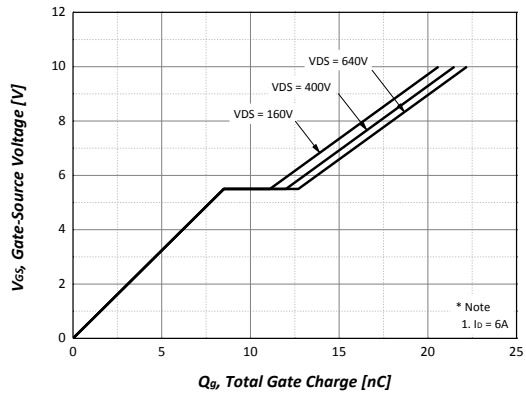
Body Diode Forward Voltage



Capacitance Characteristics

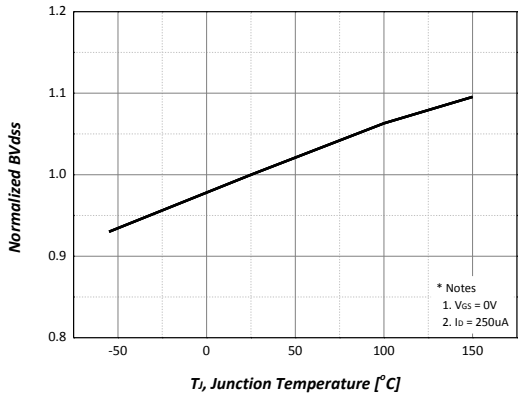


Gate Charge Characteristics

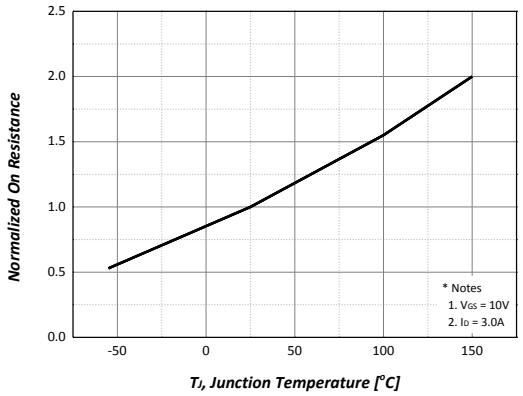


Typical Characteristics

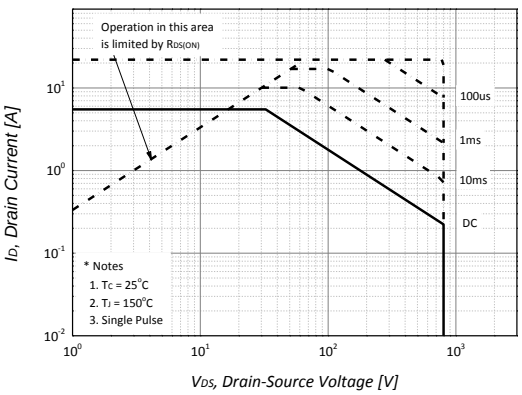
BVdss Variation vs. Temperature



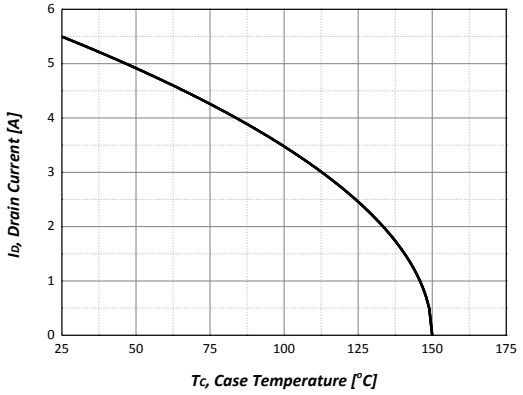
On Resistance Variation vs. Temperature



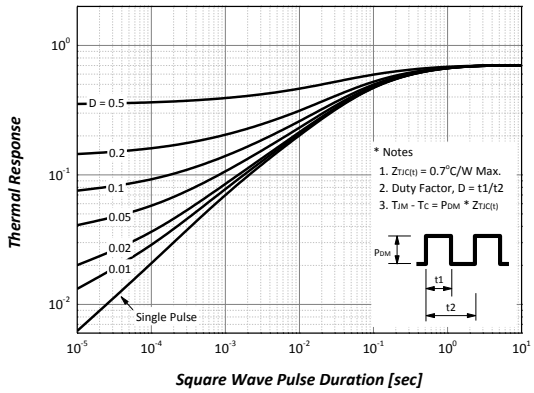
Safe Operation Area



Maximum Drain Current vs. Case Temperature



Transient Thermal Response Curve



Characteristics Test Circuit & Waveform

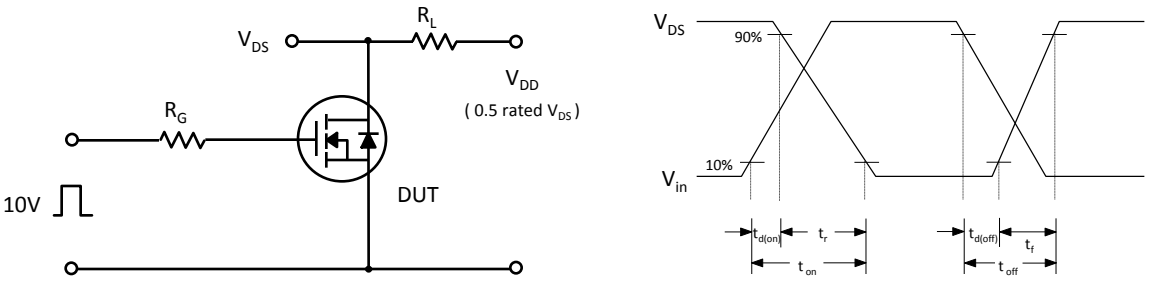


Fig 14. Resistive Switching Test Circuit & Waveforms

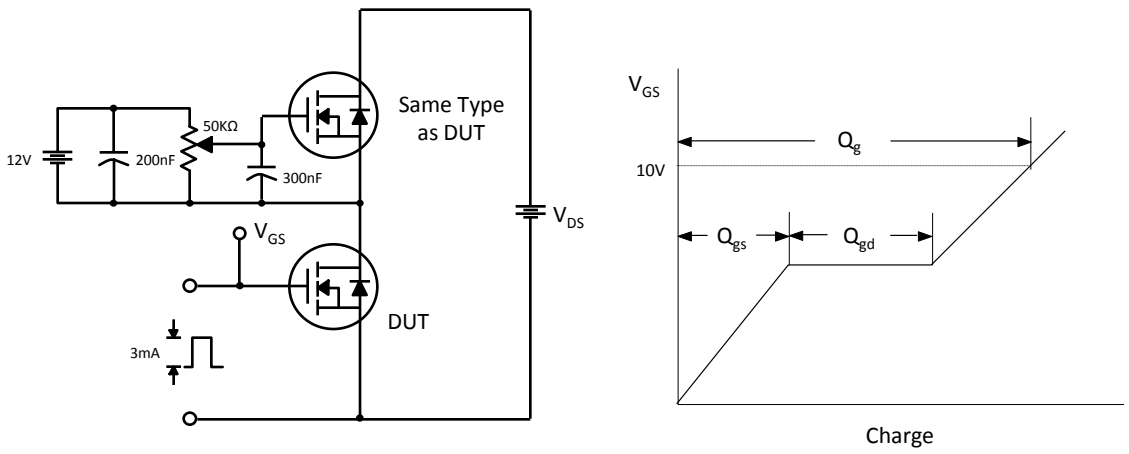


Fig 15. Gate Charge Test Circuit & Waveform

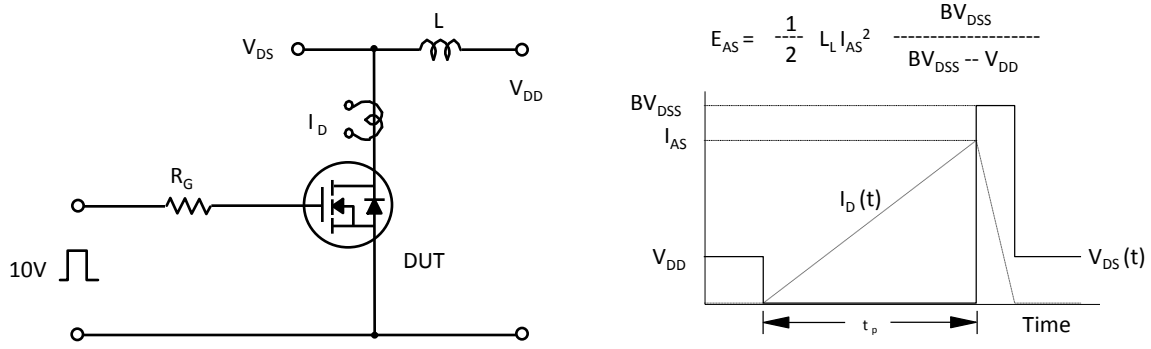
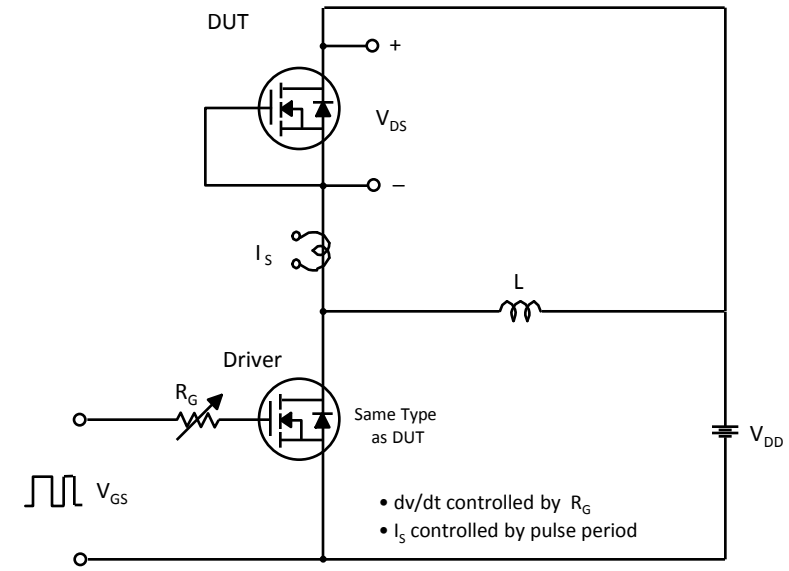


Fig 16. Unclamped Inductive Switching Test Circuit & Waveforms

Characteristics Test Circuit & Waveform (continued)



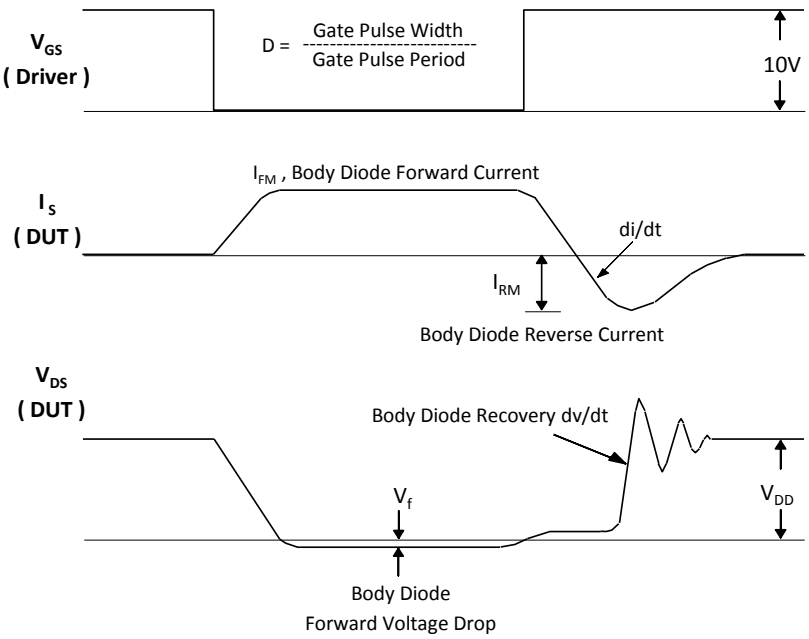


Fig 17. Peak Diode Recovery dv/dt Test Circuit & Waveforms